Unit: mm

TOSHIBA Field Effect Transistor Silicon P Channel MOS Type (U-MOSVI)

# **TPC6110**

#### **Power Management Switch Applications**

• Small footprint due to small and thin package

• Low drain-source ON resistance: RDS (ON) = 43 m $\Omega$  (typ.)

• Low leakage current:  $I_{DSS} = -10 \mu A (max) (V_{DS} = -30 V)$ 

• Enhancement mode:  $V_{th} = -0.8 \text{ to } -2.0 \text{ V}$ 

 $(V_{DS} = -10 \text{ V}, I_{D} = -0.1 \text{mA})$ 

## **Absolute Maximum Ratings (Ta = 25°C)**

Characteristics			Symbol	Rating	Unit	
Drain-source voltage			$V_{DSS}$	-30	V	
Drain-gate voltage ( $R_{GS} = 20 \text{ k}\Omega$ )			$V_{DGR}$	-30	V	
Gate-source voltage			V <sub>GSS</sub>	-25/+20	V	
Drain current	DC	(Note 1)	I <sub>D</sub>	-4.5	Α	
Drain current	Pulse	(Note 1)	I <sub>DP</sub>	-18	A	
Drain power dissipation (t = 5 s) (Note 2a)			P <sub>D</sub>	2.2	W	
Drain power dissipation (t = 5 s) (Note 2b)		P <sub>D</sub>	0.7	W		
Single pulse avalanche energy (Note 3)			E <sub>AS</sub>	3.4	mJ	
Avalanche current			I <sub>AR</sub>	-2.3	Α	
Repetitive avalanche energy (Note 4)			E <sub>AR</sub>	0.025	mJ	
Channel temperature			T <sub>ch</sub>	150	°C	
Storage temperature range			T <sub>stg</sub>	-55 to 150	°C	

1. Drain 5. Drain 3. Gate 6. Drain

JEDEC —

JEITA —

TOSHIBA 2-3T1A

Weight: 0.011 g (typ.)

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

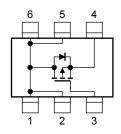
#### **Thermal Characteristics**

Characteristics	Symbol	Max	Unit
Thermal resistance, channel to ambient (t = 5 s) (Note 2a)	R <sub>th (ch-a)</sub>	56.8	°C/W
Thermal resistance, channel to ambient (t = 5 s) (Note 2b)	R <sub>th (ch-a)</sub>	178.5	°C/W

Note: (Note 1), (Note 2), (Note 3), (Note 4) and (Note 5): See other pages.

This transistor is an electrostatic-sensitive device. Please handle with caution.

#### **Circuit Configuration**



Start of commercial production 2009-08



# Electrical Characteristics (Ta = 25°C)

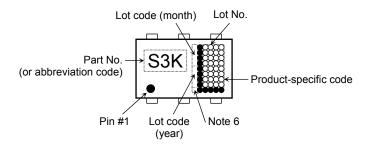
Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage cur	rent	I <sub>GSS</sub>	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$	_	_	— ±100	
Drain cut-off curre	ent	I <sub>DSS</sub>	$V_{DS} = -30 \text{ V}, V_{GS} = 0 \text{ V}$	_	_	-10	μА
Drain-source breakdown voltage		V (BR) DSS	$I_D = -10 \text{ mA}, V_{GS} = 0 \text{ V}$ -30		_	_	V
Dialii-source brea	akuowii voitage	V <sub>(BR)</sub> DSX	$I_D = -10 \text{ mA}, V_{GS} = 10 \text{ V}$ (Note 7)	-21	_	_	v
Gate threshold vo	Gate threshold voltage		$V_{DS} = -10 \text{ V}, I_D = -0.1 \text{ mA}$	-0.8	_	-2.0	V
Drain cource ON	rosistanco	Б	$V_{GS} = -4.5 \text{ V}, I_D = -2.2 \text{ A}$	_	59	77	mΩ
Drain-source ON resistance		R <sub>DS</sub> (ON)	$V_{GS} = -10 \text{ V}, I_D = -2.2 \text{ A}$	_	43	56	1117.5
Forward transfer admittance		Y <sub>fs</sub>	$V_{DS} = -10 \text{ V}, I_D = -2.2 \text{ A}$	4.2	8.4	_	S
Input capacitance		C <sub>iss</sub>		_	510	_	pF
Reverse transfer capacitance		C <sub>rss</sub>	$V_{DS} = -10 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	_	85	_	
Output capacitan	Output capacitance			_	110	_	
Switching time	Rise time	t <sub>r</sub>	$V_{CS}$ $0 \text{ V}$ $\Gamma$ $I_D = -2.2 \text{ A}$	_	6	_	- ns
	Turn-on time	t <sub>on</sub>	V <sub>GS</sub> -10 V	_	12	_	
	Fall time	t <sub>f</sub>	R = 6.	_	21	_	
	Turn-off time	t <sub>off</sub>	$V_{DD} \approx -15 \text{ V}$ Duty $\leq$ 1%, $t_W = 10 \mu\text{s}$	_	70	_	
Total gate charge (gate-source plus gate-drain)		Qg	V <sub>DD</sub> ≈ -24 V, V <sub>GS</sub> = -10 V,	_	14	_	nC
Gate-source charge 1		Q <sub>gs1</sub>	$I_D = -4.5 \text{ A}$		1.6		
Gate-drain ("miller") charge		Q <sub>gd</sub>		_	3.8	_	

## **Source-Drain Ratings and Characteristics (Ta = 25°C)**

Charact	Characteristics Symbol		Test Condition	Min	Тур.	Max	Unit
Drain reverse current	Pulse (Note 1)	I <sub>DRP</sub>	_	_	_	-18	Α
Forward voltage (diode) V <sub>DSF</sub>		V <sub>DSF</sub>	$I_{DR} = -4.5 \text{ A}, V_{GS} = 0 \text{ V}$	_	_	1.2	V

Note 7: VDSX mode (the application of a plus voltage between gate and source) may cause decrease in maximum rating of drain-source voltage.

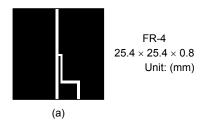
## Marking (Note 5)

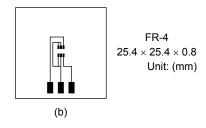


Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2: (a) Device mounted on a glass-epoxy board (a) (t = 5 s)

(b) Device mounted on a glass-epoxy board (b) (t = 5 s)





Note 3:  $V_{DD} = -24 \text{ V}$ ,  $T_{ch} = 25 ^{\circ}\text{C}$  (initial), L = 0.5 mH,  $R_G = 25 \Omega$ ,  $I_{AR} = -2.3 \text{ A}$ 

Note 4: Repetitive rating : pulse width limited by maximum channel temperature

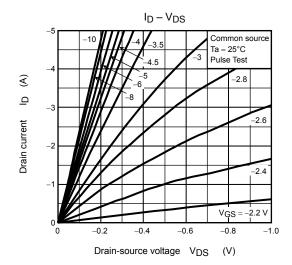
Note 5: • on lower left of the marking indicates Pin 1.

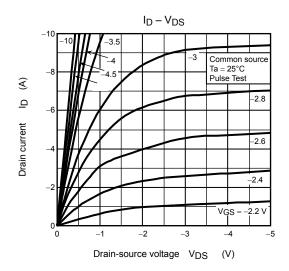
Note 6: A dot marking for identifying the indication of product Labels.

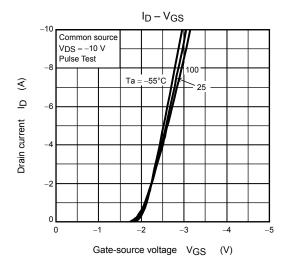
Without a dot: [[Pb]]/INCLUDES > MCV

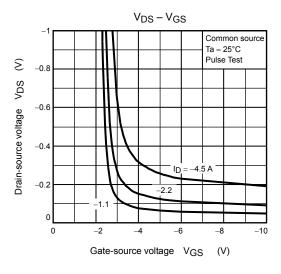
With a dot: [[G]]/RoHS COMPATIBLE or [[G]]/RoHS [[Pb]]

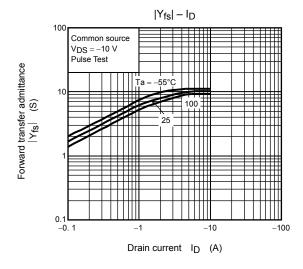
Please contact your TOSHIBA sales representative for details as to environmental matters such as the RoHS compatibility of Product. The RoHS is the Directive 2011/65/EU of the European Parliament and of the Council of 8 June 2011 on the restriction of the use of certain hazardous substances in electrical and electronic equipment.

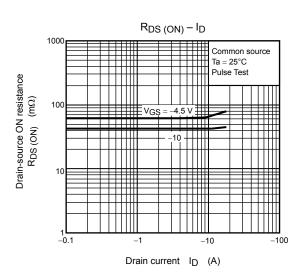


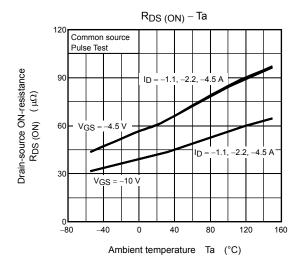


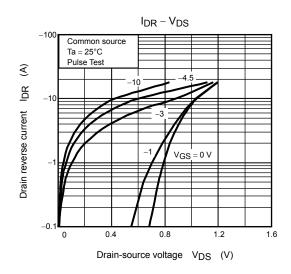


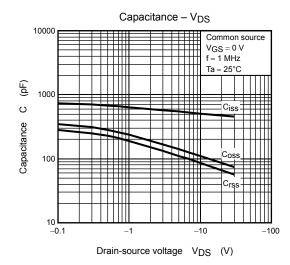


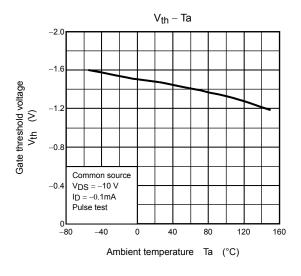


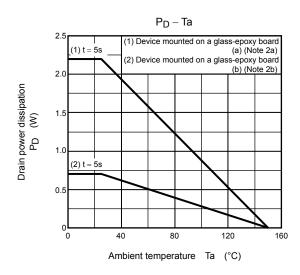


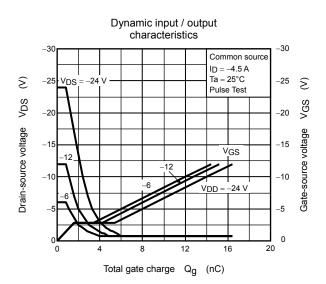




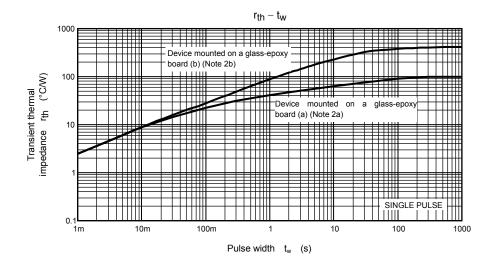


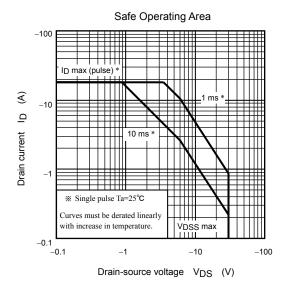






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